

BC486 BC488 BC490

PNP SILICON PLANAR EPITAXIAL TRANSISTORS

MICRO ELECTRONICS

BC486, BC488 and BC490 are PNP silicon planar epitaxial transistors designed for use as high voltage high current driver and output transistors.

CASE TO-92F



CBE

ABSOLUTE MAXIMUM RATINGS

		BC486	BC488	BC490
Collector-Base Voltage	V _{CB0}	45V	60V	80V
Collector-Emitter Voltage	V _{CE0}	45V	60V	80V
Emitter-Base Voltage	V _{EB0}		5V	
Collector Current	I _C		1A	
Total Power Dissipation @ T _A =25°C	P _{tot}		625mW	
			1.5W	
Operating Junction & Storage Temperature	T _j , T _{stg}	-55 to +150°C		

ELECTRICAL CHARACTERISTICS AT T_A=25°C

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BV _{CB0}	↑			V	I _C =0.1mA I _E =0
Collector-Emitter Breakdown Voltage	BV _{CE0}	Note 1			V	I _C =10mA I _B =0
Emitter-Base Breakdown Voltage	BV _{EB0}	↓			V	I _E =10μA I _C =0
Collector Cutoff Current	I _{CB0}			100	nA	V _{CB} =V _{CB0} I _E =0
Collector-Emitter Saturation Voltage	V _{CE(SAT)*}			0.5	V	I _C =500mA I _B =50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)*}			1.2	V	I _C =500mA I _B =50mA
D.C. Current Gain	HFE*	40				I _C =10mA V _{CE} =2V
		60		400		I _C =100mA V _{CE} =2V
		60		150		I _C =100mA V _{CE} =2V
		100		250		I _C =100mA V _{CE} =2V
		160		400		I _C =100mA V _{CE} =2V
		15				I _C =1A V _{CE} =5V
Current Gain-Bandwidth Product	f _T		75		MHz	I _C =50mA V _{CE} =2V
Output Capacitance	C _{ob}		12		pF	V _{CB} =10V I _E =0
Input Capacitance	C _{ib}		85		pF	V _{BE} =2V I _C =0

Note 1: equal to the values of the absolute maximum ratings.

* Pulse Test : Pulse Width=0.3ms, Duty Cycle=1%

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